



MJE13003

NPN SILICON TRANSISTOR

NPN SILICON POWER TRANSISTOR

■ DESCRIPTION

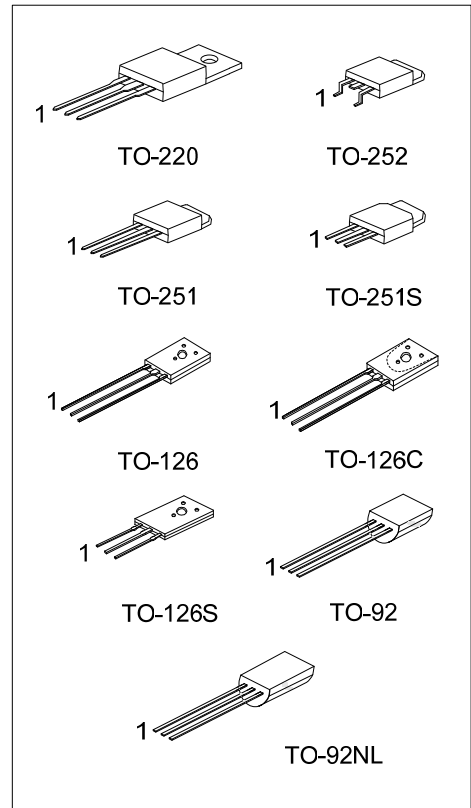
These devices are designed for high-voltage, high-speed power switching inductive circuits where fall time is critical. They are particularly suited for 115 and 220V applications in switch mode.

■ FEATURES

- * Reverse biased SOA with inductive load @ $T_C=100^{\circ}\text{C}$
- * Inductive switching matrix 0.5 ~ 1.5 Amp, 25 and 100°C
Typical $t_C = 290\text{ns}$ @ 1A, 100°C .
- * 700V blocking capability

■ APPLICATIONS

- * Switching regulator's, inverters
- * Motor controls
- * Solenoid/relay drivers
- * Deflection circuits



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen-Free		1	2	3	
MJE13003L-x-TA3-T	MJE13003G-x-TA3-T	TO-220	B	C	E	Tube
MJE13003L-x-TM3-T	MJE13003G-x-TM3-T	TO-251	B	C	E	Tube
MJE13003L-x-TMS-T	MJE13003G-x-TMS-T	TO-251S	B	C	E	Tube
MJE13003L-x-TN3-R	MJE13003G-x-TN3-R	TO-252	B	C	E	Tape Reel
MJE13003L-x-T60-K	MJE13003G-x-T60-K	TO-126	B	C	E	Bulk
MJE13003L-x-T6C-A-K	MJE13003G-x-T6C-A-K	TO-126C	E	C	B	Bulk
MJE13003L-x-T6C-K	MJE13003G-x-T6C-K	TO-126C	B	C	E	Bulk
MJE13003L-x-T6S-K	MJE13003G-x-T6S-K	TO-126S	B	C	E	Bulk
MJE13003L-x-T92-B	MJE13003G-x-T92-B	TO-92	E	C	B	Tape Box
MJE13003L-x-T92-K	MJE13003G-x-T92-K	TO-92	E	C	B	Bulk
MJE13003L-x-T92-F-B	MJE13003G-x-T92-F-B	TO-92	B	C	E	Tape Box
MJE13003L-x-T92-F-K	MJE13003G-x-T92-F-K	TO-92	B	C	E	Bulk
MJE13003L-x-T9N-B	MJE13003G-x-T9N-B	TO-92NL	E	C	B	Tape Box
MJE13003L-x-T9N-K	MJE13003G-x-T9N-K	TO-92NL	E	C	B	Bulk

Note: Pin Assignment: B: Base C: Collector E: Emitter

MJE13003L-x-T6C-A-K (1) Packing Type (2) Pin Assignment (3) Package Type (4) Rank (5) Green Package	(1) B: Tape Box, K: Bulk, R: Tape Reel, T: Tube (2) refer to Pin Assignment (for TO-126C) (3) TA3: TO-220, TM3: TO-251, TMS: TO-251S, TN3: TO-252, T60: TO-126, T6C: TO-126C, T6S: TO-126S, T92: TO-92, T9N: TO-92NL (4) x: refer to Classification of h_{FE1} (5) L: Lead Free, G: Halogen Free and Lead Free
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MARKING

TO-220 / TO-251 / TO-251S / TO-252	TO-126 / TO-126C / TO-126S
UTC MJE13003 Lot Code → Data Code L: Lead Free G: Halogen Free 1	UTC MJE13003 Pin Code → Data Code L: Lead Free G: Halogen Free 1
TO-92	TO-92NL
UTC MJE 13003 Pin Code → Data Code L: Lead Free G: Halogen Free 1	UTC MJE13003 Data Code → L: Lead Free G: Halogen Free

■ ABSOLUTE MAXIMUM RATINGS

PARAMETER			SYMBOL	RATINGS	UNIT		
Collector-Emitter Voltage			V _{CEO(SUS)}	400	V		
Collector-Base Voltage			V _{CBO}	700	V		
Collector-Emitter Voltage (V _{BE} =0)			V _{CES}	700	V		
Emitter Base Voltage			V _{EBO}	9	V		
Collector Current		Continuous	I _C	1.5	A		
		Peak (1)	I _{CM}	3			
Base Current		Continuous	I _B	0.75	A		
		Peak (1)	I _{BM}	1.5			
Emitter Current		Continuous	I _E	2.25	A		
		Peak (1)	I _{EM}	4.5			
Power Dissipation	T _A =25°C	TO-126/TO-126C TO-126S	P _D	1.4	W		
		TO-92/TO-92NL		1.1	W		
		TO-220		2	W		
		TO-251/TO-251S TO-252		1.56	W		
		T _C =25°C		TO-126/TO-126C TO-126S	20	W	
				TO-92/TO-92NL	1.5	W	
	TO-220			40	W		
	TO-251/TO-251S TO-252			25	W		
	Junction Temperature			T _J	+150	°C	
	Storage Temperature			T _{STG}	-55 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **ELECTRICAL CHARACTERISTICS** ($T_C=25^\circ\text{C}$, unless otherwise specified.)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS (Note)							
Collector-Emitter Sustaining Voltage		$V_{CEO(SUS)}$	$I_C=10mA$, $I_B=0$	400			V
Collector Cutoff Current	$T_C=25^{\circ}C$	I_{CEO}	$V_{CEO}=\text{Rated Value}$, $V_{BE(OFF)}=1.5\text{ V}$			1	mA
	$T_C=100^{\circ}C$					5	
Emitter Cutoff Current		I_{EBO}	$V_{EB}=9V$, $I_C=0$			1	mA
SECOND BREAKDOWN							
Second Breakdown Collector Current with bass forward biased		$I_{s/b}$		See Fig.5			
Clamped Inductive SOA with base reverse biased		RB_{SOA}		See Fig.6			
ON CHARACTERISTICS (Note)							
DC Current Gain		h_{FE1}	$I_C=0.5A$, $V_{CE}=5V$	14		57	
		h_{FE2}	$I_C=1A$, $V_{CE}=5V$	5		30	
Collector-Emitter Saturation Voltage		$V_{CE(SAT)}$	$I_C=0.5A$, $I_B=0.1A$			0.5	V
			$I_C=1A$, $I_B=0.25A$			1	
			$I_C=1.5A$, $I_B=0.5A$			3	
			$I_C=1A$, $I_B=0.25A$, $T_C=100^{\circ}C$			1	
Base-Emitter Saturation Voltage		$V_{BE(SAT)}$	$I_C=0.5A$, $I_B=0.1A$			1	V
			$I_C=1A$, $I_B=0.25A$			1.2	
			$I_C=1A$, $I_B=0.25A$, $T_C=100^{\circ}C$			1.1	
DYNAMIC CHARACTERISTICS							
Current-Gain-Bandwidth Product		f_T	$I_C=100mA$, $V_{CE}=10V$, $f=1MHz$	4	10		MHz
Output Capacitance		C_{OB}	$V_{CB}=10V$, $I_E=0$, $f=0.1MHz$		21		pF
SWITCHING CHARACTERISTICS							
Resistive Load (Table 1)							
Delay Time	t_D	$V_{CC}=125V$, $I_C=1A$, $I_{B1}=I_{B2}=0.2A$, $t_P=25\mu s$, Duty Cycles $\leq 1\%$		0.05	0.1	μs	
Rise Time	t_R			0.5	1	μs	
Storage Time	t_S			2	4	μs	
Fall Time	t_F			0.4	0.7	μs	
Inductive Load, Clamped (Table 1)							
Storage Time	t_{STG}	$I_C=1A$, $V_{CLAMP}=300V$, $I_{B1}=0.2A$, $V_{BE(OFF)}=5V_{DC}$, $T_C=100^{\circ}C$		1.7	4	μs	
Crossover Time	t_C			0.29	0.75	μs	
Fall Time	t_F			0.15		μs	

Note: Pulse Test: $PW=300\mu\text{s}$, Duty Cycle $\leq 2\%$

■ **CLASSIFICATION OF h_{FE1}**

RANK	A	B	C	D	E	F	G	H
RANGE	14 ~ 22	21 ~ 27	26 ~ 32	31 ~ 37	36 ~ 42	41 ~ 47	46 ~ 52	51 ~ 57

■ APPLICATION INFORMATION

Table 1. Test Conditions for Dynamic Performance

	Reverse Bias Safe Operating Area and Inductive Switching	Resistive Switching
Test Circuits	DUTY CYCLE 10% tr, tf 10ns Note: P_W and V_{CC} Adjusted for Desired I_C R_B Adjusted for Desired I_{B1} SELECTED FOR 1kV	
Circuit Values	Coil Data : GAP for 30 mH/2 A $V_{CC}=20V$ Ferrocube core #6656 $V_{CLAMP}=300V$ Full Bobbin (~ 200 Turns) #20 $L_{COIL}=50mH$	$V_{CC}=125V$ $R_C=125\Omega$ $D1=1N5820$ or Equiv. $R_C=47\Omega$
Test Waveforms	t_1 Adjusted to Obtain I_C $t_{1j} \dot{U} \frac{L_{COIL}(I_{cpk})}{V_{CC}}$ $t_{2j} \dot{U} \frac{L_{COIL}(I_{cpk})}{V_{CLAMP}}$ Test Equipment Scope-Tektronics 475 or Equivalent	tr, tf < 10ns Duty Cycle = 1.0% Rs and Rc adjusted for desired Is and Ic

Table 2. Typical Inductive Switching Performance

I _C (A)	T _C (°C)	t _{sv} (μs)	t _{RV} (μs)	t _{FI} (μs)	t _{TI} (μs)	t _C (μs)
0.5	25 100	1.3 1.6	0.23 0.26	0.30 0.30	0.35 0.40	0.30 0.36
1	25 100	1.5 1.7	0.10 0.13	0.14 0.26	0.05 0.06	0.16 0.29
1.5	25 100	1.8 3	0.07 0.08	0.10 0.22	0.05 0.08	0.16 0.28

Note: All Data Recorded in the Inductive Switching
Circuit in Table 1

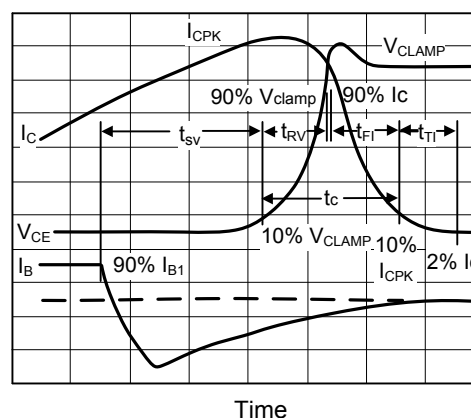


Fig.1 Inductive Switching Measurements

SWITCHING TIMES NOTE

In resistive switching circuits, rise, fall, and storage times have been defined and apply to both current and voltage waveforms since they are in phase. However, for inductive loads, which are common to switch mode power supplies and hammer drivers, current and voltage waveforms are not in phase. Therefore, separate measurements must be made on each waveform to determine the total switching time. For this reason, the following new terms have been defined.

t_{SV} = Voltage Storage Time, 90% I_{B1} to 10% V_{CLAMP}

t_{RV} = Voltage Rise Time, 10 ~ 90% V_{CLAMP}

t_{FI} = Current Fall Time, 90 ~ 10% I_C

t_{TI} = Current Tail, 10 ~ 2% I_C

t_C = Crossover Time, 10% V_{CLAMP} to 10% I_C

For the designer, there is minimal switching loss during storage time and the predominant switching power losses occur during the crossover interval and can be obtained using the standard equation:

$$P_{SWT} = 1/2 V_{CC} I_C (t_C) f$$

In general, $t_{RV} + t_{FI} \approx t_C$. However, at lower test currents this relationship may not be valid.

As is common with most switching transistors, resistive switching is specified at 25°C and has become a benchmark for designers. However, for designers of high frequency converter circuits, the user oriented specifications which make this transistor are the inductive switching speeds (t_C and t_{SV}) which are guaranteed at 100°C.

RESISTIVE SWITCHING PERFORMANCE

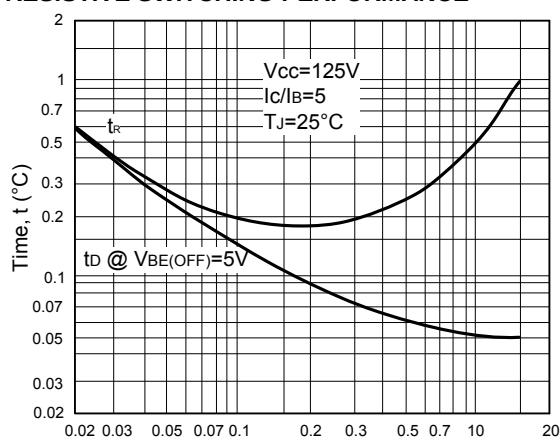


Fig.2 Turn-On Time

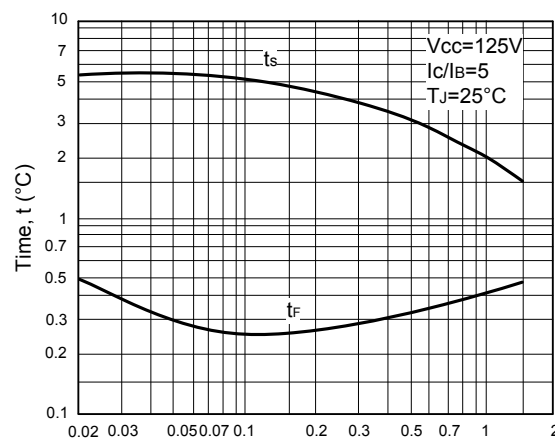


Fig.3 Turn-Off Time

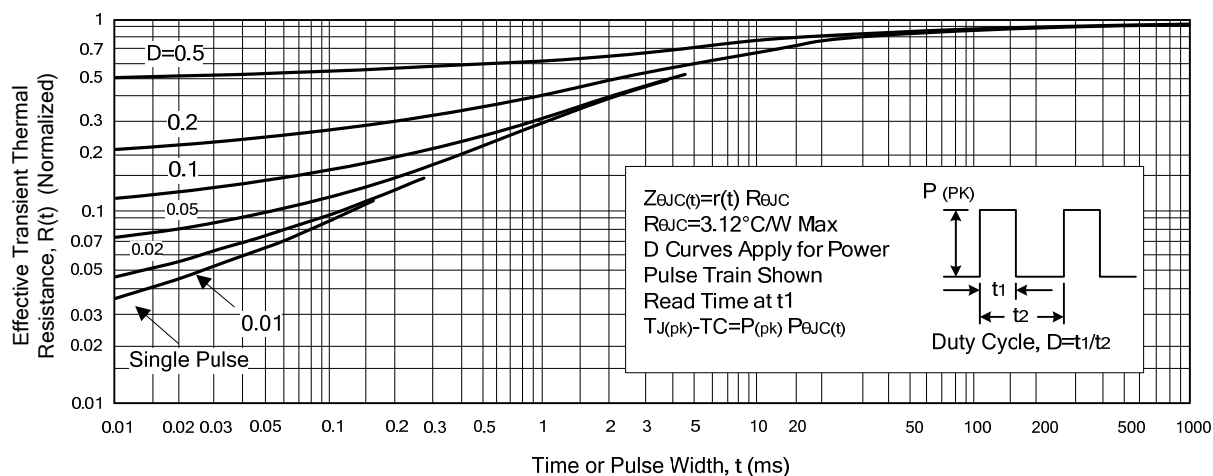


Fig.4 Thermal Response

■ SAFE OPERATING AREA INFORMATION

FORWARD BIAS

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Fig.5 is based on $T_C = 25^\circ\text{C}$; $T_{J(PK)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C \geq 25^\circ\text{C}$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Fig.5.

$T_{J(PK)}$ may be calculated from the data in Fig.4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

REVERSE BIAS

For inductive loads, high voltage and high current must be sustained simultaneously during turn-off, in most cases, with the base to emitter junction reverse biased. Under these conditions the collector voltage must be held to a safe level at or below a specific value of collector current. This can be accomplished by several means such as active clamping, RC snubbing, load line shaping, etc. The safe level for these devices is specified as RB_{SOA} (Reverse Bias Safe Operating Area) and represents the voltage-current conditions during reverse biased turn-off. This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode. Fig.6 gives RB_{SOA} characteristics.

The Safe Operating Area of Fig.5 and 6 are specified ratings (for these devices under the test conditions shown.)

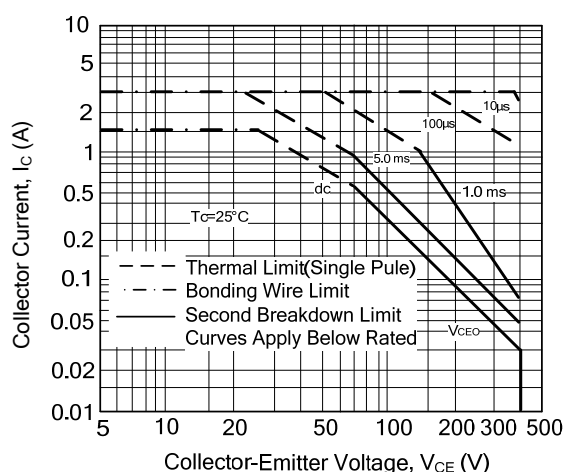


Fig.5 Active Region Safe Operating Area

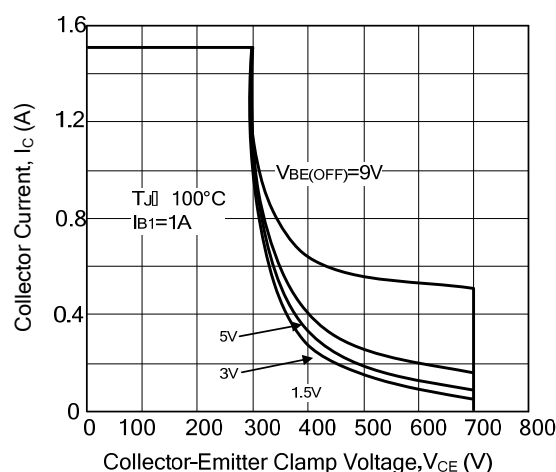
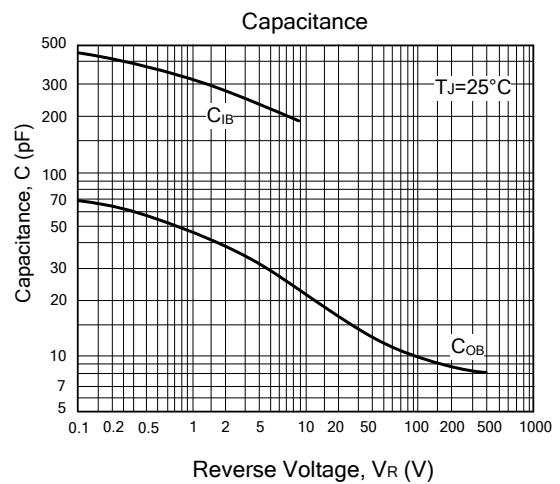
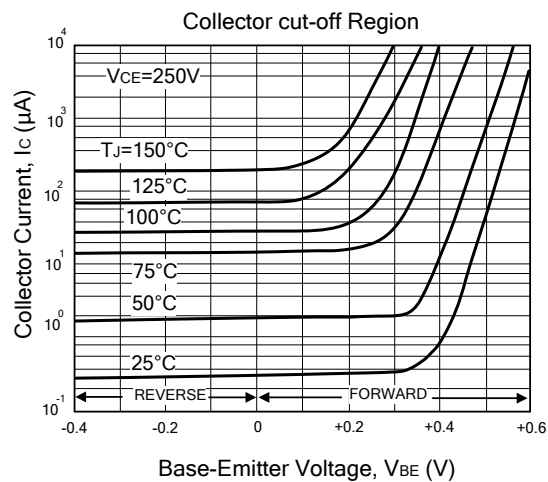
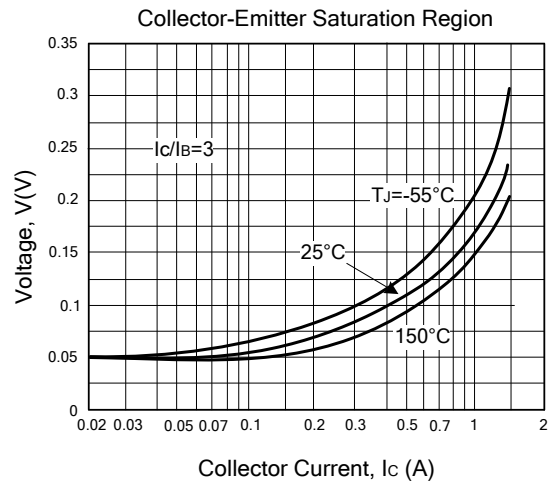
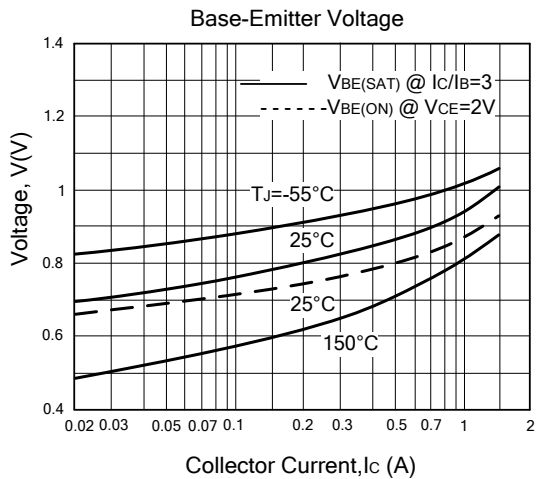
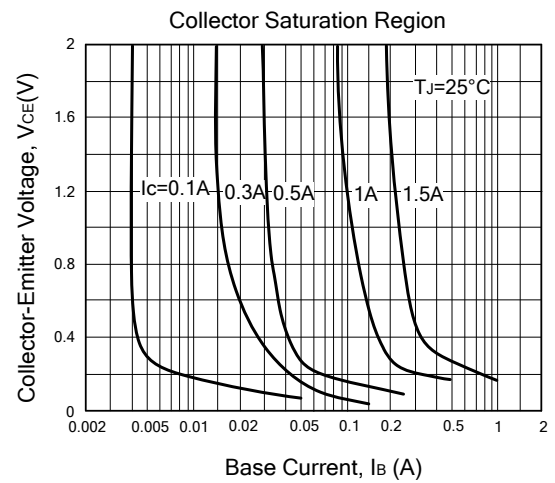
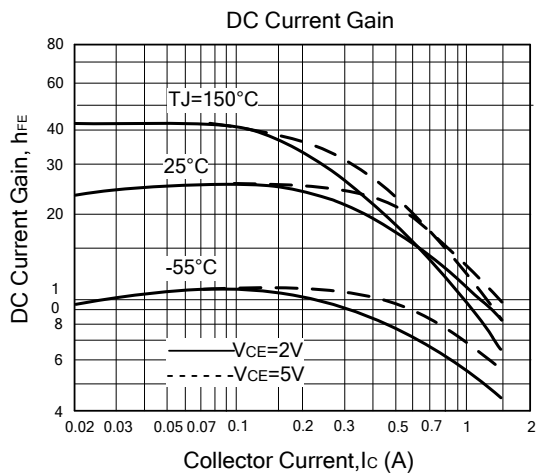
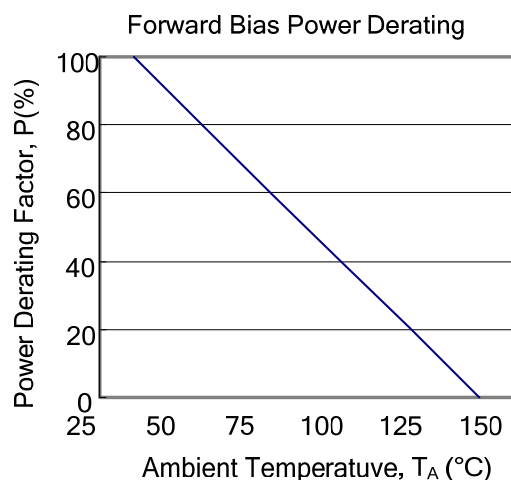


Fig.6 Reverse Bias Safe Operating Area

■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



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